

ABSTRACT

According to one exemplary embodiment, a structure situated in a semiconductor die comprises an active shield situated in a substrate, where the active shield comprises a salicide layer situated on an active region, and where the active shield has a first

5 conductivity type. The active shield can be situated in a well in the substrate, where the well is connected to a voltage source greater than or equal to a ground voltage, and where the well has a second conductivity type. According to this exemplary embodiment, the structure further comprises a passive component situated in an interconnect metal layer in the semiconductor die, where the passive component is situated above the active shield,

10 and where the active shield defines an AC ground for the passive component. The structure further comprises at least one contact, where the at least one contact connects the active shield to a semiconductor die AC ground.